



30V P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	Rds(on) Max	I _D Max T _C = +25°C
-30V	15mΩ @ V _{GS} = -10V	-42A
	$25m\Omega$ @ V _{GS} = -5V	-32A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Backlighting
- Power management functions
- DC-DC converters

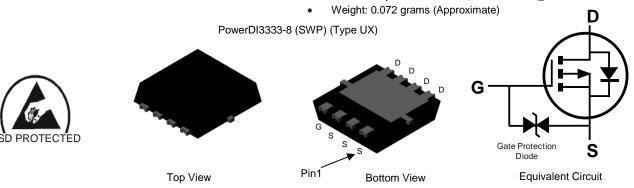
Features and Benefits

- Low R_{DS(ON)} ensures on-state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DIODES™ DMP3021SFVWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: PowerDI[®]3333-8
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 ⁽³⁾



Ordering Information (Note 4)

Part Number	Packago	Packing		
Part Number	Package	Qty.	Carrier	
DMP3021SFVWQ-7	PowerDI3333-8 (SWP) (Type UX)	2,000	Tape & Reel	
DMP3021SFVWQ-13	PowerDI3333-8 (SWP) (Type UX)	3,000	Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



 $\frac{\text{SW2}}{\text{YY}} = \text{Product Type Marking Code} \\ \frac{\text{YY}}{\text{YY}} = \text{Date Code Marking} \\ \frac{\text{YY}}{\text{YY}} = \text{Last Two Digits of Year (ex: 22 = 2022)} \\ \text{WW} = \text{Week Code (01 to 53)} \\$



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			VDSS	-30	V
Gate-Source Voltage	V_{GSS}	±25	V		
Continuous Drain Current (Note 6) V _{GS} = -10V	Steady State	T _A = +25°C T _A = +70°C	lo	-11 -9	А
Continuous Drain Current (Note 7) V _{GS} = -10V	Steady State	$T_C = +25^{\circ}C$ $T_C = +70^{\circ}C$	lo	-42 -34	А
Maximum Continuous Body Diode Forward Currer	Is	-42	Α		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			Ірм	-128	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			I _{SM}	-128	Α
Avalanche Current (Note 8) L = 1mH	las	-13	А		
Avalanche Energy (Note 8) L = 1mH	Eas	84	mJ		

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	1	W
Thermal Resistance, Junction to Ambient (Note 5) Steady State		Reja	126.6	°C/W
Total Power Dissipation (Note 6) $T_A = +25^{\circ}C$		P _D	2.5	W
Thermal Resistance, Junction to Ambient (Note 6) Steady State		Reja	51.2	°C/W
Thermal Resistance, Junction to Case (Note 7)	R ₀ JC	3.6	°C/W	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

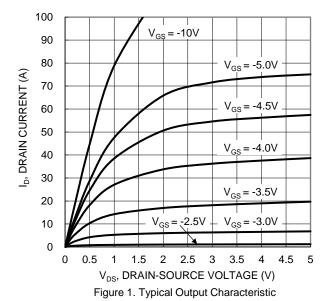
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

,	-,		- /				
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current	IDSS	_	_	-1	μA	V _{DS} = -30V, V _{GS} = 0V	
Gate-Source Leakage	lgss	_	_	±10	μA	$V_{GS} = \pm 25V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	Vgs(TH)	-1.0	_	-2.5	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$	
Static Drain-Source On-Resistance	Process	_	10.3	15	mΩ	$V_{GS} = -10V, I_D = -8A$	
Static Dialii-Source Off-Resistance	RDS(ON)		15.5	25	11122	$V_{GS} = -5V, I_{D} = -5A$	
Diode Forward Voltage	VsD	_	-0.7	-1.2	V	V _G S = 0V, I _S = -1A	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss	_	1799	_	pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss	_	259	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	225	_	pF		
Gate Resistance	Rg	_	2.1	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1.0MHz$	
Total Gate Charge (V _{GS} = -5V)	Qg	_	17.4	_	nC		
Total Gate Charge (V _{GS} = -10V)	Qg	_	34	_	nC	V _{DS} = -15V, I _D = -10A	
Gate-Source Charge	Qgs	_	5.1	_	nC		
Gate-Drain Charge	Qgd		8.4	_	nC		
Turn-On Delay Time	t _{D(ON)}	_	6.5	_	ns		
Turn-On Rise Time	tR	_	18.3	_	ns	$V_{DD} = -15V$, $V_{GS} = -10V$, $R_{G} = 3\Omega$, $I_{D} = -10A$	
Turn-Off Delay Time	t _D (OFF)	_	35.8	_	ns		
Turn-Off Fall Time	tr	_	23.7	_	ns		
Reverse Recovery Time	trr	_	14.9	_	ns	I- 00 dl/dt 5000///-	
Reverse Recovery Charge	Qrr	_	15	_	nC	$\frac{1}{1}$ Is = -8A, dI/dt = 500A/ μ s	

5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided. Notes:

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to product testing.





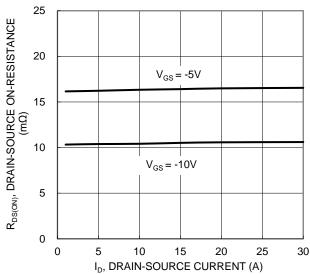


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

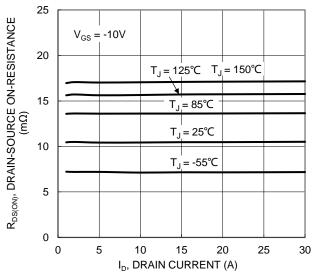


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

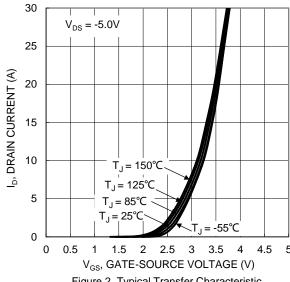


Figure 2. Typical Transfer Characteristic

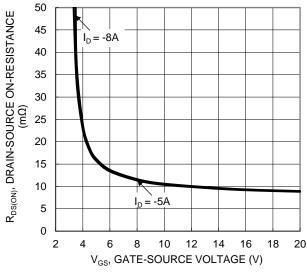


Figure 4. Typical Transfer Characteristic

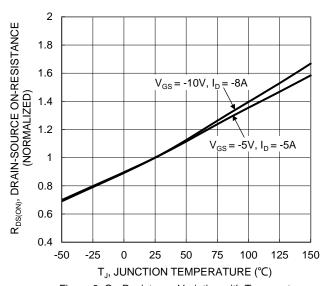


Figure 6. On-Resistance Variation with Temperature





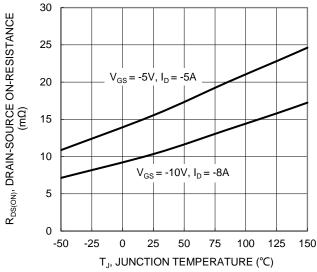
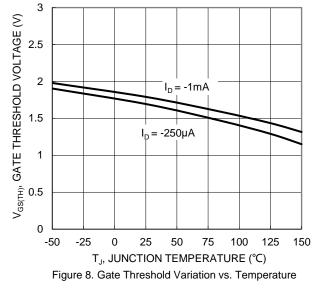
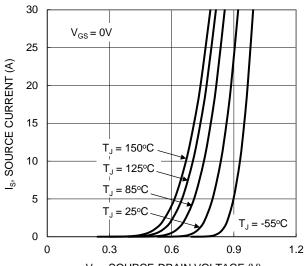
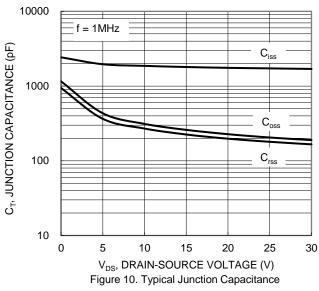


Figure 7. On-Resistance Variation with Temperature





 V_{SD} , SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current



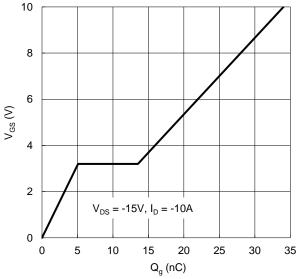


Figure 11. Gate Charge

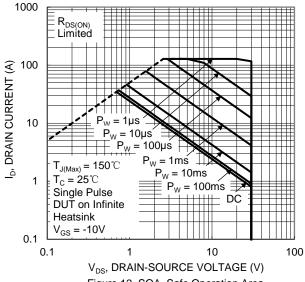


Figure 12. SOA, Safe Operation Area



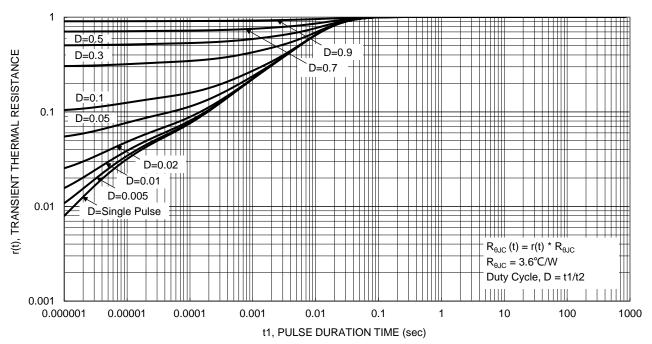


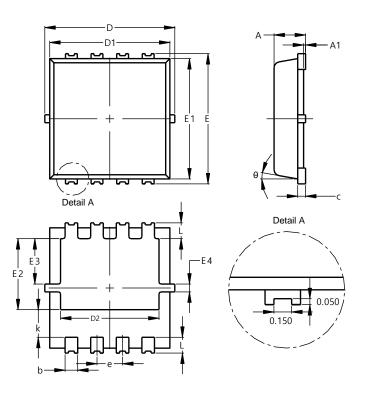
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)

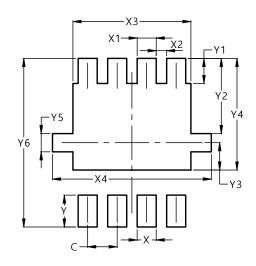


PowerDI3333-8 (SWP)						
(Type UX)						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05				
b	0.25	0.40	0.32			
C	0.10	0.25	0.15			
D	3.20	3.40	3.30			
D1	2.95	3.15	3.05			
D2	2.30	2.70	2.50			
Е	3.20	3.40	3.30			
E1	2.95	3.15	3.05			
E2	1.60	2.00	1.80			
E3	0.95	1.35	1.15			
E4	0.10	0.30	0.20			
е	_	_	0.65			
k	0.50	0.90	0.70			
L	0.30	0.50	0.40			
θ	0°	12°	10°			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)		
С	0.650		
Х	0.420		
X1	0.420		
X2	0.230		
Х3	2.600		
X4	3.500		
Υ	0.700		
Y1	0.550		
Y2	1.650		
Y3	0.600		
Y4	2.450		
Y5	0.400		
Y6	3.700		



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